

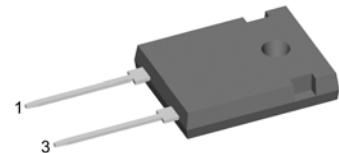
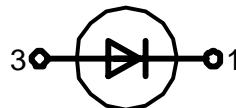
Sonic-FRD

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

V_{RRM} = 600 V
I_{FAV} = 30 A
t_{rr} = 35 ns

Part number (Marking on product)

DHG 30 I 600HA

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm}-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- TO-247AD
- Industry standard outline
 - Epoxy meets UL 94V-0
 - RoHS compliant

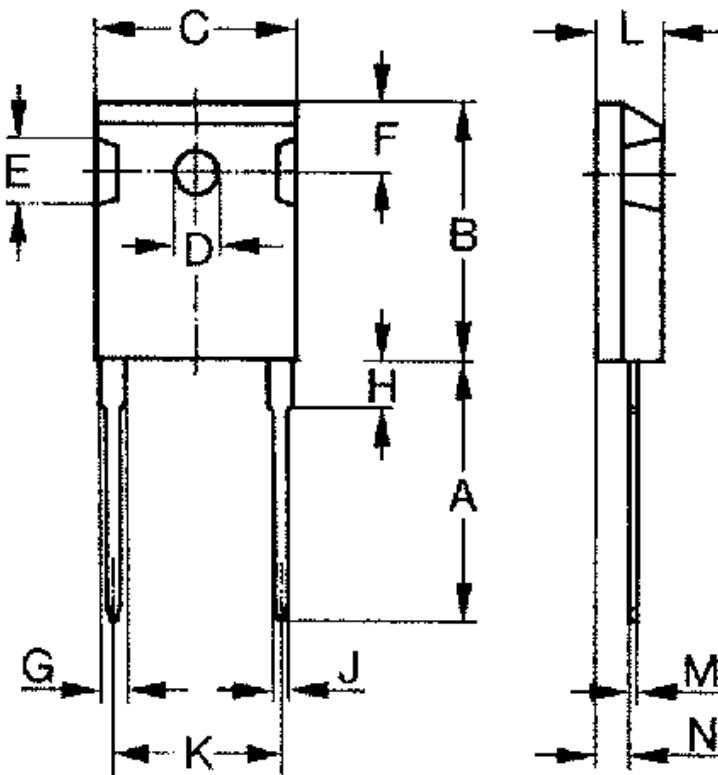
Ratings						
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V _{RRM}	max. repetitive reverse voltage	T _{vj} = 25 °C			600	V
I _R	reverse current	V _R = 600 V T _{vj} = 25 °C V _R = 600 V T _{vj} = 125 °C			50 5	µA mA
V _F	forward voltage	I _F = 30 A T _{vj} = 25 °C I _F = 60 A I _F = 30 A T _{vj} = 125 °C I _F = 60 A			2.36 2.20	V V
I _{FAV}	average forward current	rectangular, d = 0.5 T _c = 85 °C			30	A
V _{F0} r _F	threshold voltage slope resistance } for power loss calculation only				1.31 28.6	V mΩ
R _{thJC}	thermal resistance junction to case				0.70	K/W
T _{vj}	virtual junction temperature		-55		150	°C
P _{tot}	total power dissipation	T _c = 25 °C			180	W
I _{FSM}	max. forward surge current	t _p = 10 ms (50 Hz), sine T _{vj} = 45 °C			200	A
I _{RM}	max. reverse recovery current	I _F = 30 A; T _{vj} = 25 °C -di _F /dt = 600 A/µs T _{vj} = 125 °C			12	A
t _{rr}	reverse recovery time	V _R = 400 V T _{vj} = 25 °C T _{vj} = 125 °C		35		ns
C _J	junction capacitance	V _R = 300 V; f = 1 MHz T _{vj} = 25 °C				pF
E _{AS}	non-repetitive avalanche energy	I _{AS} = A; L = 100 µH T _{vj} = 25 °C			tbd	mJ
I _{AR}	repetitive avalanche current	V _A = 1.5 · V _R typ.; f = 10 kHz			tbd	A

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per pin*			70	A
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
M_D	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N
T_{stg}	storage temperature		-55		150	°C
Weight				6		g

* I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Outlines TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102